

SUMMARY OF THE INVENTION

The present invention provides a method of manufacturing a semiconductor device comprising steps of:

forming a first metal film having a reducing property on a semiconductor substrate;

thermal treating the resulting semiconductor substrate for reducing a native oxide film naturally formed on the semiconductor substrate and for forming a first silicide film on the semiconductor substrate;

removing an unreacted first metal film selectively;

forming a second metal film on the semiconductor substrate;

and

thermal treating the resulting semiconductor substrate for forming a second silicide film on a surface of the semiconductor substrate which includes a region where the first silicide film is formed.

Further, according to the present invention, there is provided a semiconductor device manufactured by the above described method.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1A to 1D are process sectional views showing an embodiment of the present invention.

FIGS. 2A to 2D are process sectional views showing another embodiment of the present invention.

FIGS. 3A to 3D are process sectional views showing an